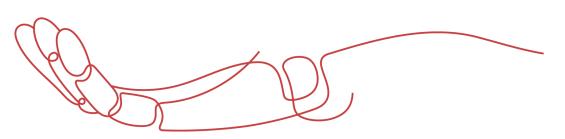


PRODUCT DATA SHEET



To learn more about JGSEMI, please visit our website at







Datasheet

Samples

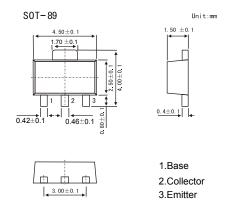
Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.



NPN Transistors

■ Features

- Low saturation voltage
- Collector-emitter voltage =60V
- Pc = 2W (on 40X40X0.7mm ceramic board).
- Complements the 2SB1561.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit	
Collector - Base Voltage	Vсво	60	٧	
Collector - Emitter Voltage	VCEO	60		
Emitter - Base Voltage	VEBO	6		
Collector Current - Continuous	lc 2		Α	
Collector Current - Pulse (Note.1)	ICP	6	A	
Collector Power Dissipation (Note.2)	Pc	0.5	W	
		2		
Junction Temperature	TJ	150	$^{\circ}$ C	
Storage Temperature Range	Tstg	-55 to 150	C	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Collector- base breakdown voltage	Vсво	Ic= 100 μA, IE= 0	60				
Collector- emitter breakdown voltage	VCEO	Ic= 1 mA, I _B = 0	60			V	
Emitter - base breakdown voltage	VEBO	IE= 100 μ A, IC= 0	6				
Collector-base cut-off current	Ісво	V _{CB} = 50 V , I _E = 0			100	nA	
Emitter cut-off current	ІЕВО	V _{EB} = 5V , I _C =0			100	IIA	
Collector-emitter saturation voltage	VCE(sat)	Ic=1 A, IB=50mA			0.35	V	
Base - emitter saturation voltage	VBE(sat)	Ic=1 A, IB=50mA			1.2	V	
DC current gain	hFE(1)	VcE= 2V, Ic= 500mA	82		390		
	hFE(2)	VCE= 2V, IC= 1.5A	45				
Collector output capacitance	Cob	V _{CB} = 10V, I _E = 0,f=1MHz		21		pF	
Transition frequency	f⊤	Vce= 2V, Ie= -500mA,f=100MHz		210		MHz	



■ Typical Characterisitics

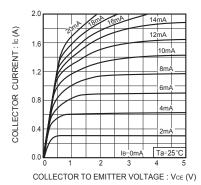


Fig.1 Grounded emitter output characteristics

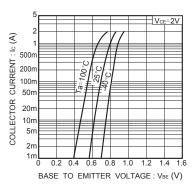


Fig.2 Grounded emitter propagation characteristics

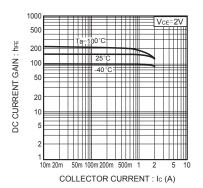


Fig.3 DC current gain vs. collector current (1)

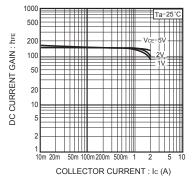


Fig.4 DC current gain vs. collector current (2)

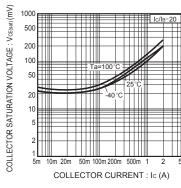


Fig.5 Collector-emitter saturation voltage vs. collector current (1)

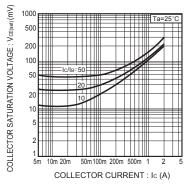


Fig.6 Collector-emitter saturation voltage vs. collector current (2)

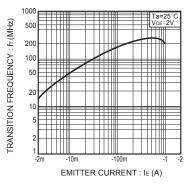


Fig.7 Gain bandwidth product vs. emitter current

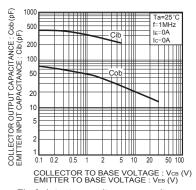


Fig.8 lutput capacitance vs. voltage

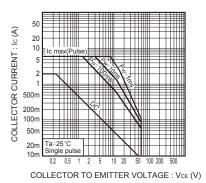


Fig.9 Safe operating area



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